

## ABSTRACT

5 A method for manufacturing a gate structure of a memory comprises the steps of  
providing a substrate; forming a plurality of gates on the surface of said substrate, each gate  
having a metal layer; forming a photoresist layer of a predetermined pattern on the surface of  
said substrate and on said gates to selectively form an opening between two of said gates;  
removing a portion of said metal layer in said gate adjacent to said opening; removing said  
photoresist layer; and forming an insulating layer on the sidewalls of said gate.

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